

SANYO Semiconductors DATA SHEET



N-Channel Silicon MOSFETs FSS802 — General-Purpose Switching Device **Applications**

Features

· Low ON-resistance.

• 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	۱D		12	А
Drain Current (PW≤10s)	۱D	duty cycle≤1%	14	А
Drain Current (PW≤10µs)	IDP	duty cycle≤1%	52	А
Allowable Power Dissipation	PD	Mounted on a ceramic board (1200mm ² X0.8mm) PW≤10s	3.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =12A	9.6	16		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	ID=12A, VGS=10V		9	13	mΩ
	RDS(on)2	ID=6A, VGS=4.5V		14	21	mΩ
	R _{DS} (on)3	ID=6A, VGS=4V		17	26	mΩ
Input Capacitance	Ciss	VDS=10V, f=1MHz		2300		pF
Output Capacitance	Coss	VDS=10V, f=1MHz		430		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		300		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit		17		ns
Rise Time	tr	See specified Test Circuit		200		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		150		ns
Fall Time	tf	See specified Test Circuit		130		ns
Marking : S802				Co	ontinued on	next page.

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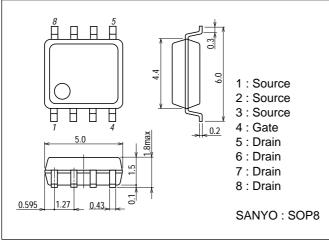
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Continued from preceding page.						
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	VDS=10V, VGS=10V, ID=12A		33		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =12A		5		nC
Gate-to-Drain "Miller" Charge	Qgd	VDS=10V, VGS=10V, ID=12A		6		nC
Diode Forward Voltage	VSD	IS=12A, VGS=0		0.81	1.2	V

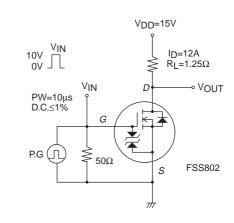
Package Dimensions

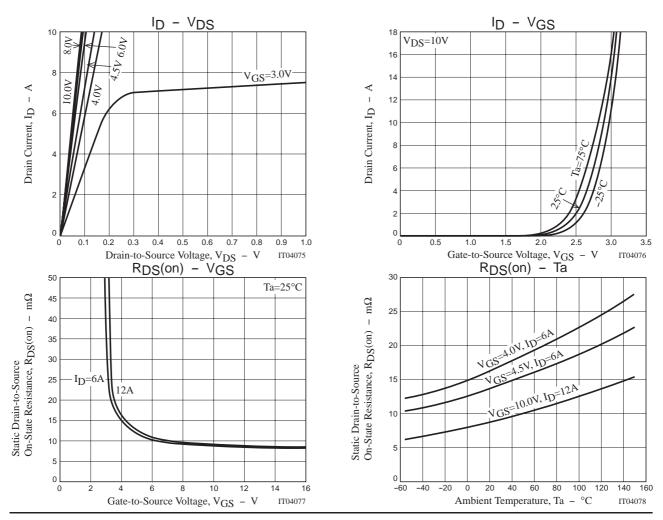
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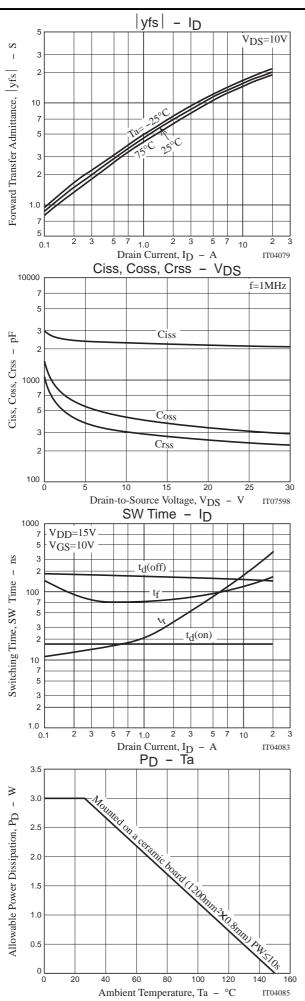
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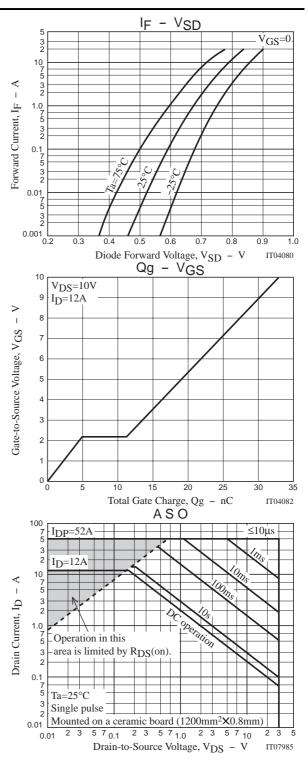


Switching Time Test Circuit









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